	Substitute for fo	orm 1449	VPTO	Complete if Known		
INFO		יסוח ו	CLOSURE	Application No.	10/661,037	
			PPLICANT	Filing Date	September 12, 2003	
SIAI	CIVICINI) I A	PLICANI	First Named Inventor	John D. Hyde	
				Art Unit	2822	
				Examiner Name	Ida M. Soward	
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Filing Date	September 12, 2003	
SIAI	CIVICINI) i Ai	PLICANT	First Named Inventor	John D. Hyde	
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				Art Unit	2822		
				Examiner Name	Ida M. Soward		
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Sheet	5	of	6	Attorney Docket Number	22524-17802	

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